

Silicon NPN Power Transistors

2SC3297

DESCRIPTION

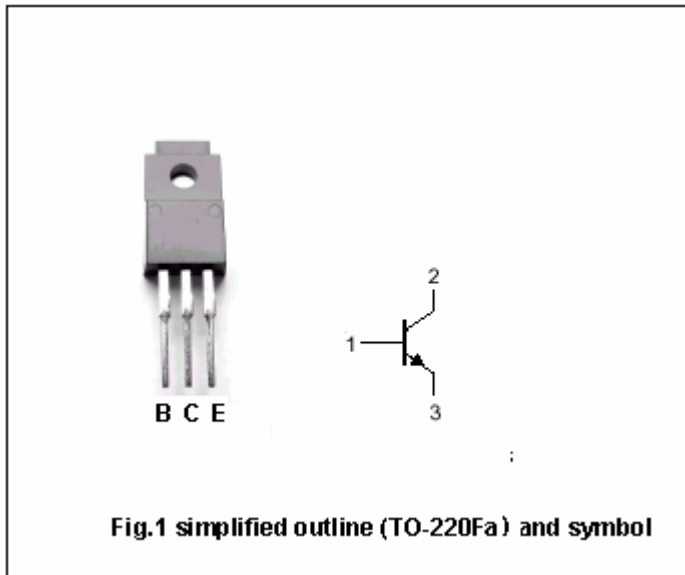
- With TO-220Fa package
- Low saturation voltage
- High speed switching time

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	30	V
V _{CEO}	Collector-emitter voltage	Open base	30	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		3	A
P _C	Collector power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA , I _B =0	30			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA , I _E =0	30			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA , I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A ; I _B =0.2A			1.0	V
V _{BE}	Base-emitter on voltage	I _C =0.5A ; V _{CE} =5V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =30V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =2V	70		280	
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		100		MHz

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PACKAGE OUTLINE

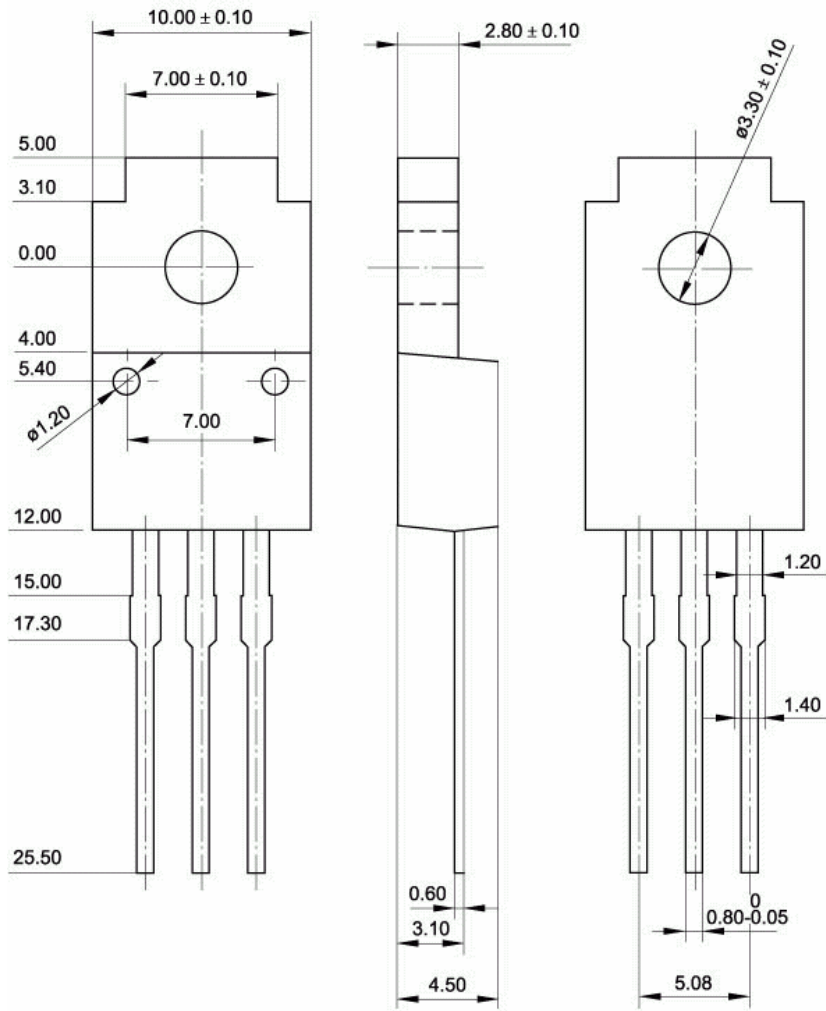


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)